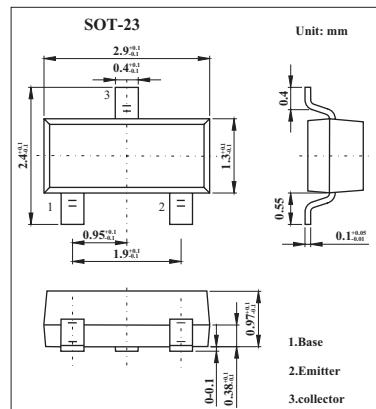


Silicon NPN Epitaxial

2SC3265

■ Features

- High DC current gain: hFE (1) = 100320.
- Low saturation voltage: $V_{CE(sat)} = 0.4$ V (max)
($I_C = 500$ mA, $I_B = 20$ mA).



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Base current	I_B	160	mA
Collector power dissipation	P_c	200	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 30$ V, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 50$ V, $I_C = 0$			0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10$ mA, $I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1$ mA, $I_C = 0$	5			V
DC current gain	hFE	$V_{CE} = 1$ V, $I_C = 100$ mA	100	320		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500$ mA, $I_B = 20$ mA			0.4	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1$ V, $I_C = 10$ mA	0.5		0.8	V
Transition frequency	f_T	$V_{CE} = 5$ V, $I_C = 10$ mA		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10$ V, $I_E = 0$, $f = 1$ MHz		13		pF

■ hFE Classification

Marking	EO	EY
hFE	100~200	160~320